

32-Channel High Voltage Sample and Hold Amplifier Array

Features

- ▶ 32 independent high voltage amplifiers
- ▶ 300V operating voltage
- ▶ 295V output voltage
- ▶ 2.2V/ μ s typical output slew rate
- ▶ Adjustable output current source limit
- ▶ Adjustable output current sink limit
- ▶ Internal closed loop gain of 72V/V
- ▶ 12M Ω feedback impedance
- ▶ Layout ideal for die applications

Applications

- ▶ MEMS (microelectromechanical systems) driver
- ▶ Piezoelectric transducer driver
- ▶ Optical crosspoint switches (using MEMS technology)

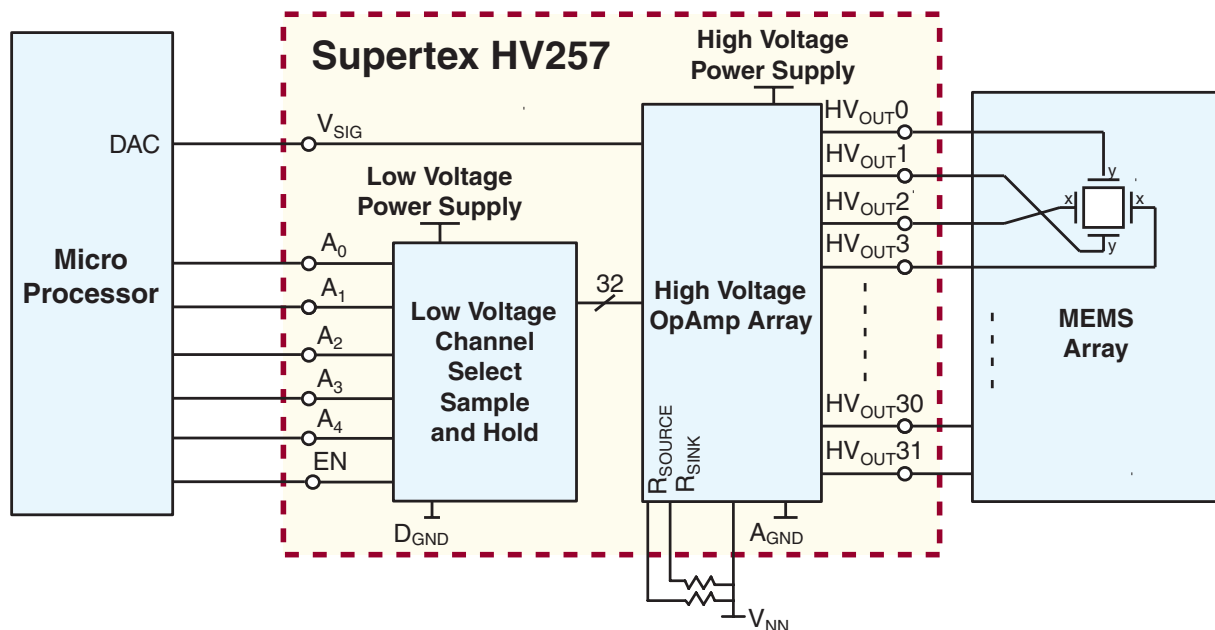
General Description

The Supertex HV257 is a 32 channel high voltage sample and hold amplifier array integrated circuit. It operates on a single high voltage supply, up to 300V, and two low voltage supplies, V_{DD} and V_{NN} .

All 32 sample and hold circuits share a common analog input, V_{SIG} . The individual sample and hold circuits are selected by a 5 to 32 logic decoder. The sampled voltage on the holding capacitor is buffered by a low voltage amplifier and amplified by a high voltage amplifier with a closed loop gain of 72V/V. The internal closed loop gain is set for an input voltage range of 0V to 4.096V. The input voltage can be up to 5.0V but the output will saturate. The maximum output voltage swing is 5V below the V_{PP} high voltage supply. The outputs can drive capacitive loads of up to 3000pF.

The maximum output source and sink current can be adjusted by using two external resistors. An external R_{SOURCE} resistor controls the maximum sourcing current, and an external R_{SINK} resistor controls the maximum sinking current. The current limit is approximated 12.5V divided by the external resistor value. The setting is common for all 32 outputs. A low voltage silicon junction diode is made available to help monitor the die temperature.

Typical Application Circuit



Absolute Maximum Ratings

V_{PP} , High voltage supply	310V
AV_{DD} , Analog low voltage positive supply	8.0V
DV_{DD} , Digital low voltage positive supply	8.0V
AV_{NN} , Analog low voltage negative supply	-7.0V
DV_{NN} , Digital low voltage negative supply	-7.0V
Logic input voltage	-0.5V to DV_{DD}
V_{SIG} , Analog input signal	0V to 6.0V
SRV_{PP} , V_{PP} ramp up/down	TBDV/usec
Storage temperature range	-65°C to 150°C
Maximum junction temperature	150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Device	Package Options
	100 Lead MQFP
HV257	HV257FG
	HV257FG-G

-G indicates package is RoHS compliant ('Green')



Operating Conditions

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{PP}	High voltage positive supply	125	-	300	V	---
V_{DD}	Low voltage positive supply	6.0	-	7.5	V	---
V_{NN}	Low voltage negative supply	-4.5	-	-6.5	V	---
I_{PP}	V_{PP} supply current	-	-	0.8	mA	$V_{PP} = 300V$, All $HV_{OUT} = 0V$ No load
I_{DD}	V_{DD} supply current	-	-	5.0	mA	$V_{DD} = 6.0V$ to $7.5V$
I_{NN}	V_{NN} supply current	-6.0	-	-	mA	$V_{NN} = -4.5V$ to $-6.5V$
T_J	Operating temperature range	-10	-	85	°C	---

Electrical Characteristics (over operating conditions, unless otherwise specified)

High Voltage Amplifier

Symbol	Parameter	Min	Typ	Max	Units	Conditions
HV_{OUT}	HV_{OUT} voltage swing	0	-	$V_{PP}-5$	V	---
V_{INOS}	Input offset	-	-	± 50	mV	Input referred
SR	HV_{OUT} slew rate rise	-	2.2	-	V/ μ s	No Load
	HV_{OUT} slew rate fall	-	2.0	-	V/ μ s	No Load
BW	HV_{OUT} -3dB channel bandwidth	-	4.0	-	KHz	$V_{PP} = 300V$
A_O	Open loop gain	70	100	-	dB	---
A_V	Closed loop gain	68.4	72	75.6	V/V	---
R_{FB}	Feedback resistance from HV_{OUT} to ground	9.6	12	-	M Ω	---
C_{LOAD}	HV_{OUT} † capacitive load	0	-	3000	pF	---
I_{SOURCE}	HV_{OUT} sourcing current limiting range	50	-	500	μ A	$I_{SOURCE} = 12.5V/R_{SOURCE}$
I_{SINK}	HV_{OUT} sinking current limiting range	50	-	500	μ A	$I_{SINK} = 12.5V/R_{SINK}$
R_{SOURCE}	External resistance range for setting maximum current source	25	-	250	K Ω	---
R_{SINK}	External resistance range for setting maximum current sink	25	-	250	K Ω	---
CT_{DC}	DC channel to channel crosstalk	-80	-	-	dB	---
PSRR	Power supply rejection ratio for V_{PP} , V_{DD} , V_{NN}	-40	-	-	dB	---

Electrical Characteristics (over operating conditions, unless otherwise specified)

Sample and Hold

Symbol	Parameter	Min	Typ	Max	Units	Conditions
t_{AQ}	Acquisition time	-	4.0	-	μs	---
V_{PED}	Pedestal voltage	-	1.0	-	mV	input referred
R_{SW}	Sample and Hold Switch resistance	-	5.0	-	k Ω	---
C_H	Sample and Hold capacitor	-	10	12	pF	---
V_{DROOP}	Voltage droop rate during hold time relative to input	-	6.0	-	V/s	output referred
V_{SIG}	Input signal voltage range	0	-	5.0	V	---
C_{SIG}	V_{SIG} input capacitance	-	33	-	pF	---

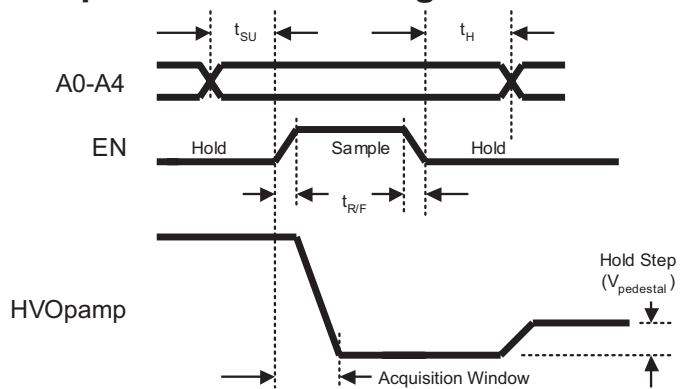
Logic Decoder

Symbol	Parameter	Min	Typ	Max	Units	Conditions
t_{SU}	Set-up time-address to enable	75	-	-	ns	---
t_H	Hold time-address to enable bar	75	-	-	ns	---
V_{IH}	Input logic high voltage	2.4	-	V_{DD}	V	---
V_{IL}	Input logic low voltage	0	-	1.2	V	---
I_{IH}	Input logic high current	-	-	1.0	μA	$V_{IL} = V_{DD}$
I_{IL}	Input logic low current	-1.0	-	-	μA	$V_{IL} = 0\text{V}$
C_{IN}	Logic input capacitance	-	-	15	pF	---

Decoder Truth Table

A_4	A_3	A_2	A_1	A_0	EN	Selected S/H
L	L	L	L	L	H	0
L	L	L	L	H	H	1
L	L	L	H	L	H	2
L	L	L	H	H	H	3
H	H	H	H	L	H	30
H	H	H	H	H	H	31
X	X	X	X	X	L	All Open

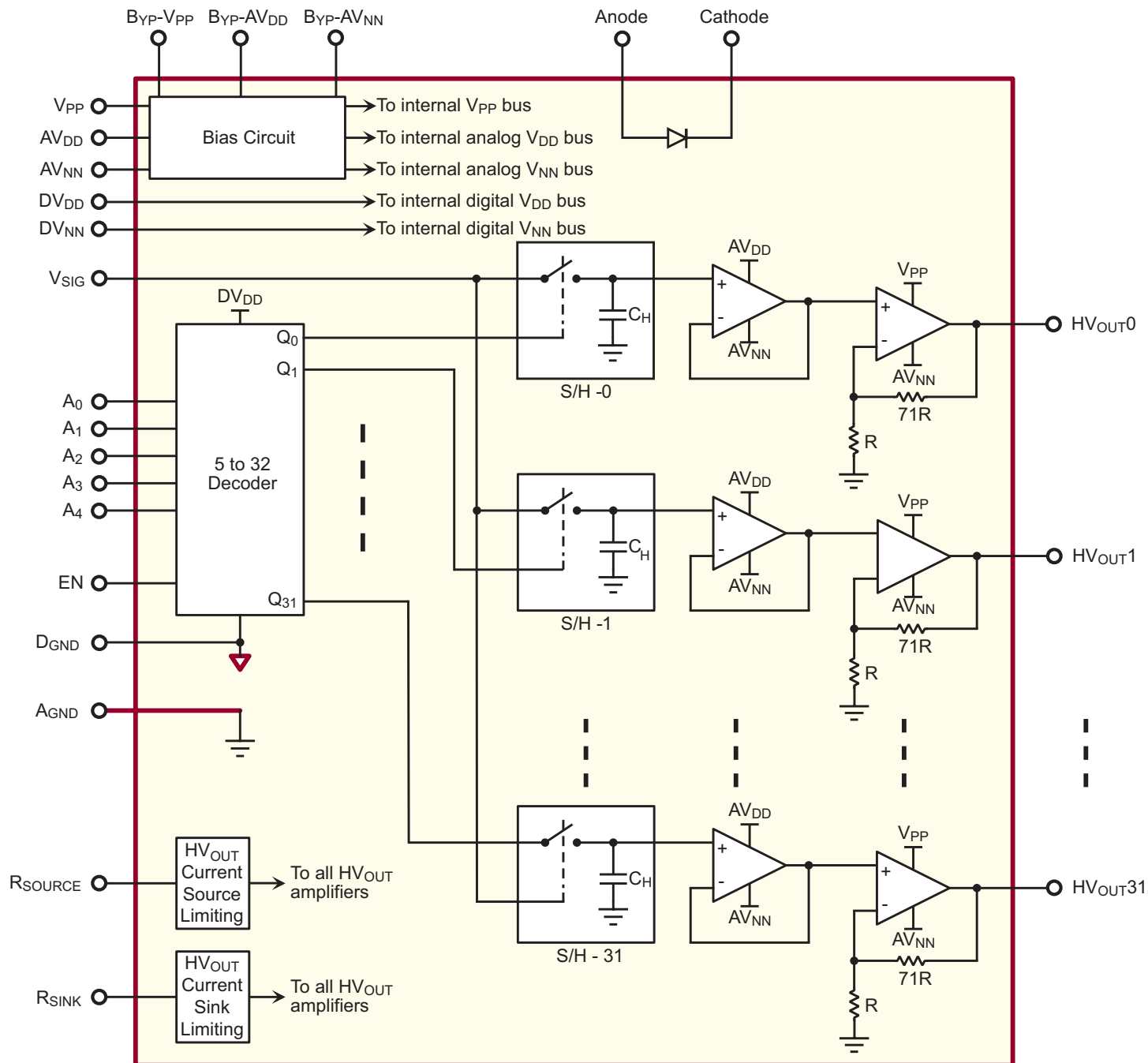
Sample and Hold Timing



Temperature Diode

Symbol	Parameter	Min	Typ	Max	Units	Conditions
PIV	Peak inverse voltage	-	-	5.0	V	cathode to anode
V_F	Forward diode drop	-	0.6	-	V	$I_F = 100\mu\text{A}$, anode to cathode at $T_A = 25^\circ\text{C}$
I_F	Forward diode current	-	-	100	μA	anode to cathode
T_C	V_F temperature coefficient	-	-2.2	-	mV/ $^\circ\text{C}$	anode to cathode

Block Diagram



Power Up/Down Issues

External Diode Protection

The device can be damaged due to improper power up / down sequence. To prevent damage, please follow the acceptable power up / down sequences, and add two external diodes as shown in the diagram on the right. The first diode is a high voltage diode across V_{PP} and V_{DD} , where the anode of the diode is connected to V_{DD} and the cathode of the diode is connected to V_{PP} . Any low current, high voltage diode, such as a 1N4004, will be adequate. The second diode is a Schottky diode across V_{NN} and D_{GND} , where the anode of the Schottky diode is connected to V_{NN} , and the cathode is connected to D_{GND} . Any low current Schottky diode such as a 1N5817 will be adequate.

Acceptable Power Up Sequences

The HV257 can be powered up with any of the following sequences listed below.

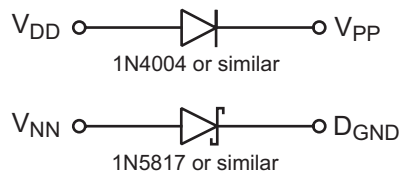
- 1) V_{PP} 2) V_{NN} 3) V_{DD} 4) Inputs and Anode
- 1) V_{NN} 2) V_{DD} 3) V_{PP} 4) Inputs and Anode
- 1) V_{DD} & V_{NN} 2) Inputs 3) V_{PP} 4) Anode

Acceptable Power Down Sequences

The HV257 can be powered down with any of the following sequences listed below.

- 1) Inputs and Anode 2) V_{DD} 3) V_{NN} 4) V_{PP}
- 1) Inputs and Anode 2) V_{PP} 3) V_{DD} 4) V_{NN}
- 1) Anode 2) V_{PP} 3) Inputs 4) V_{NN} & V_{DD}

External Diode Protection Connection

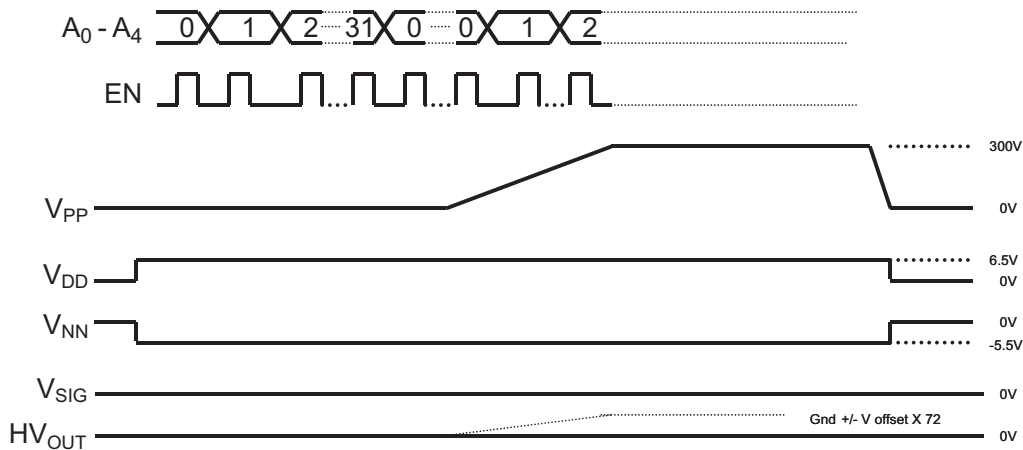


Suggested Power Up/Down Sequence

The HV257 needs all power supplies to be fully up and all channels refreshed with $V_{SIG} = 0V$ to force all high voltage outputs to 0V. Before that time, the high voltage outputs may have temporary voltage excursions above or below Gnd level depending on selected power up sequence. To minimize the excursions:

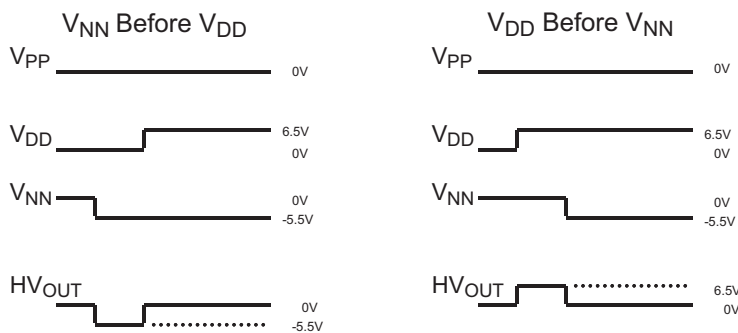
1. The V_{DD} and V_{NN} power supplies should be applied at the same time (or within a few nanoseconds).
2. All channels should be continuously refreshed with $V_{SIG} = 0V$, just before, and while the V_{PP} is ramping up. Suggested V_{PP} ramp up speed should be 10msec or longer and ramp down to be 1msec or longer.

Recommended Power Up/Down Timing



HV_{OUT} Level at Power UP

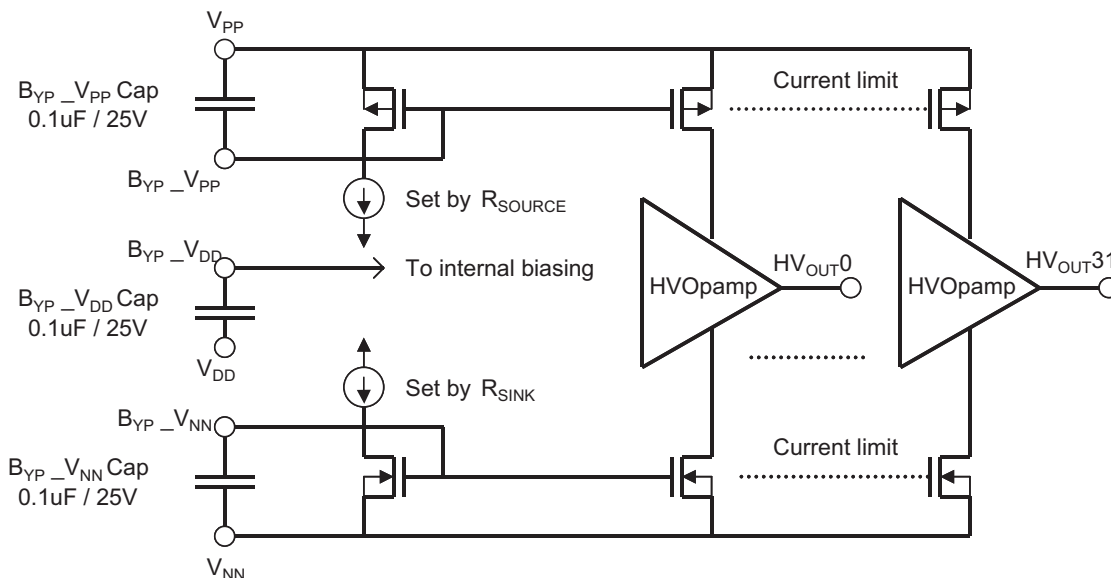
Power Up Sequence



R_{SINK} / R_{SOURCE}

The V_{DD_BYP} , V_{DD_BYP} , and V_{NN_BYP} pins are internal, high impedance current mirror gate nodes, brought out to maintain stable opamp biasing currents in noisy power supply environments. 0.1uF/25V bypass capacitors, added from V_{PP_BYP} pin to V_{PP} , from V_{DD_BYP} pin to V_{DD} , and from V_{NN_BYP} to V_{NN} , will force the high impedance gate

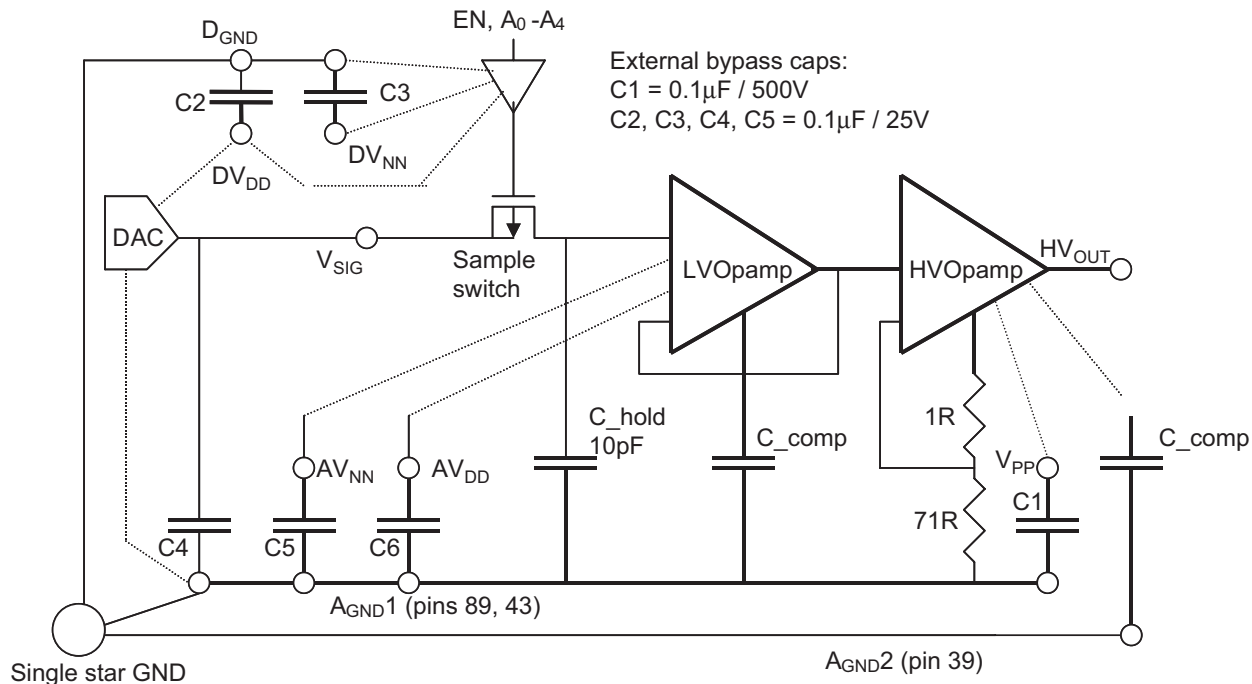
nodes to follow fluctuation of power lines. The expected voltages at the V_{DD_BYP} and V_{NN_BYP} pins are typically 1.5 volts from their respectful power supply. The expected voltage at V_{PP_BYP} is typically 3V below V_{PP} .



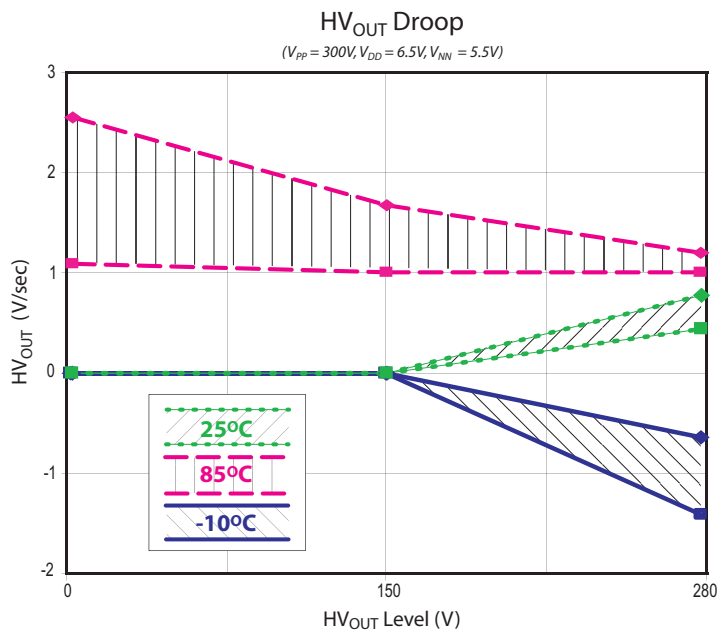
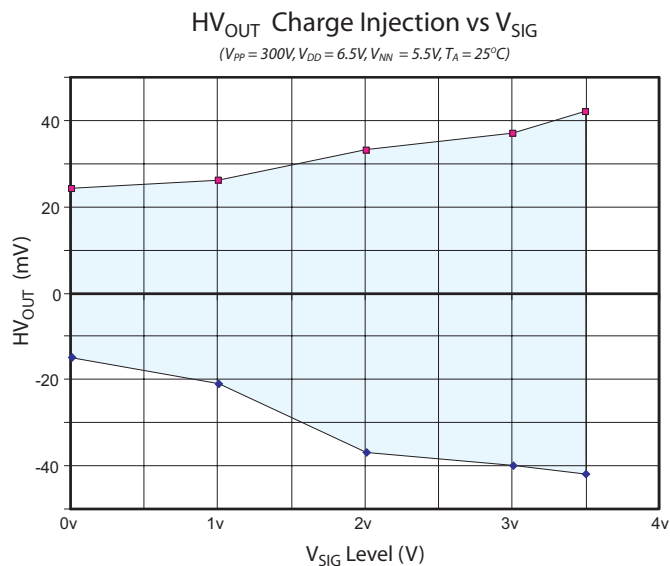
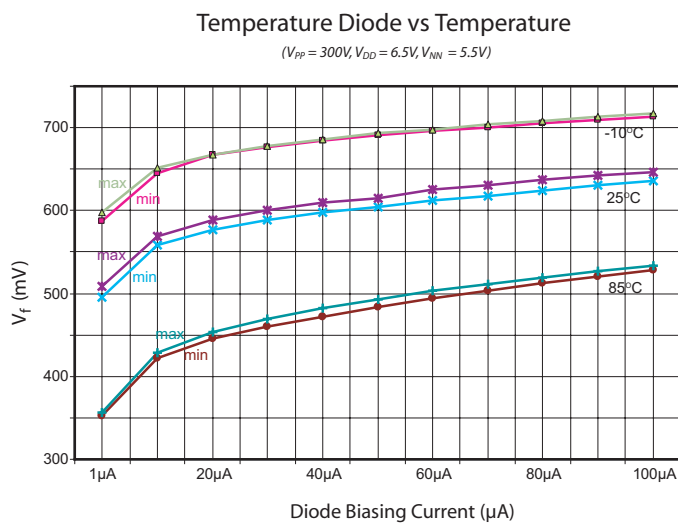
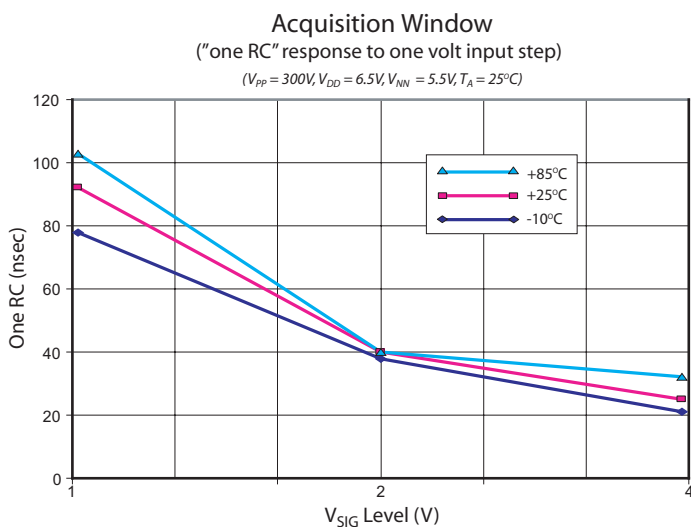
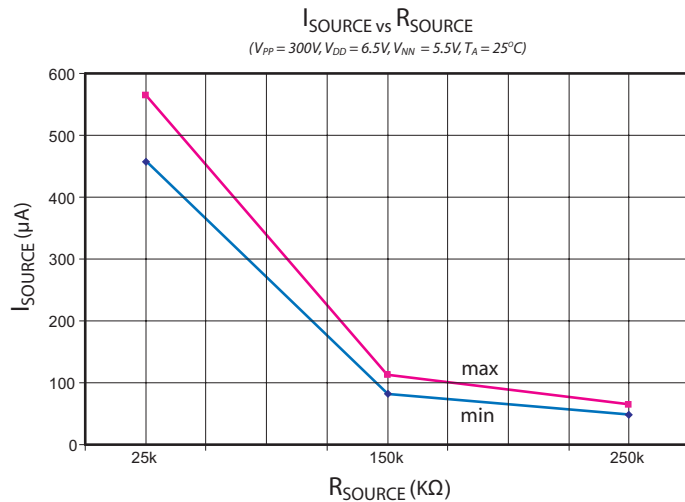
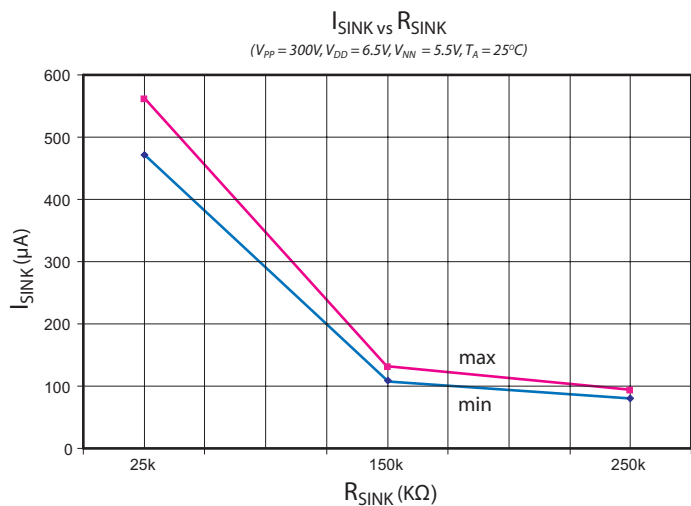
Ground Isolation (A_{GND} / D_{GND} Isolation)

It is important that the A_{GND} pin is connected to a clean ground. The hold capacitors are internally connected to the A_{GND} , and any ground noise will directly couple to the high voltage outputs (with

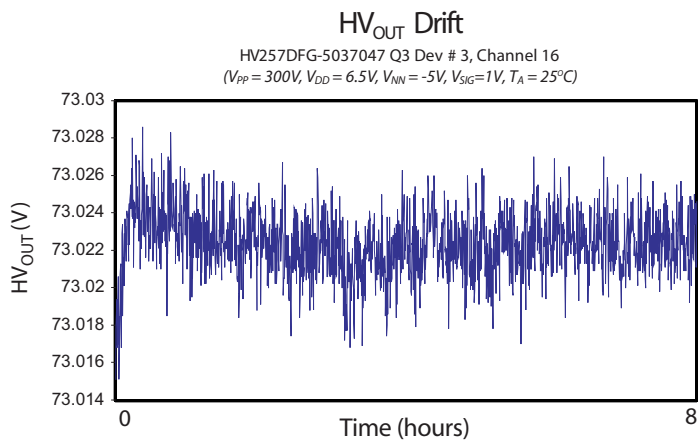
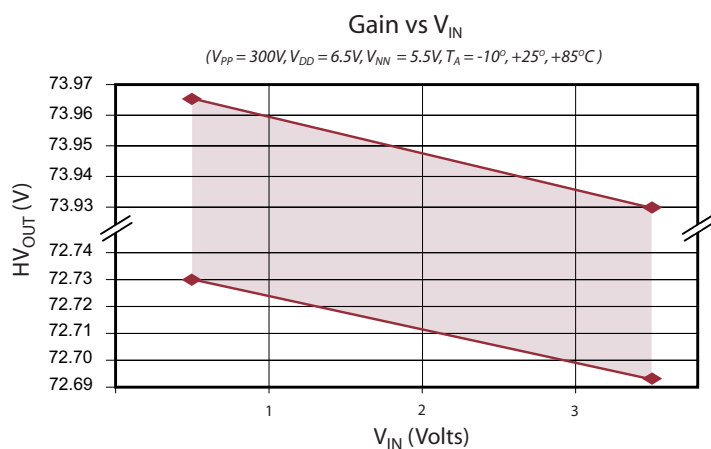
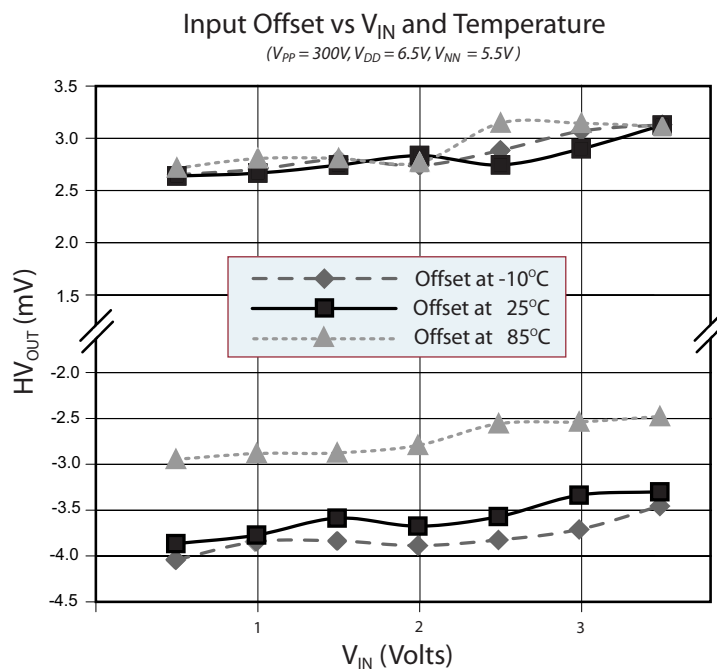
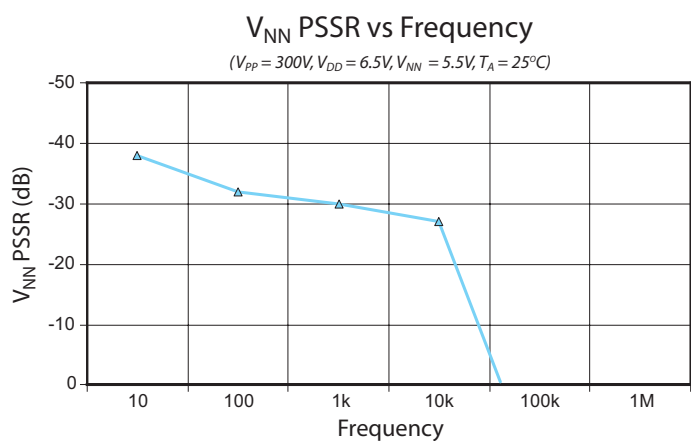
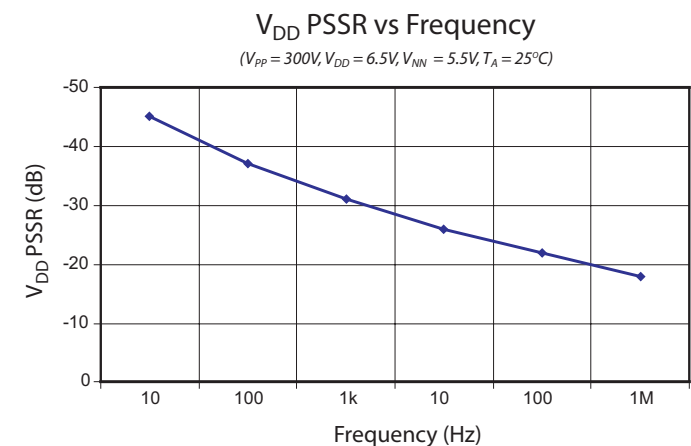
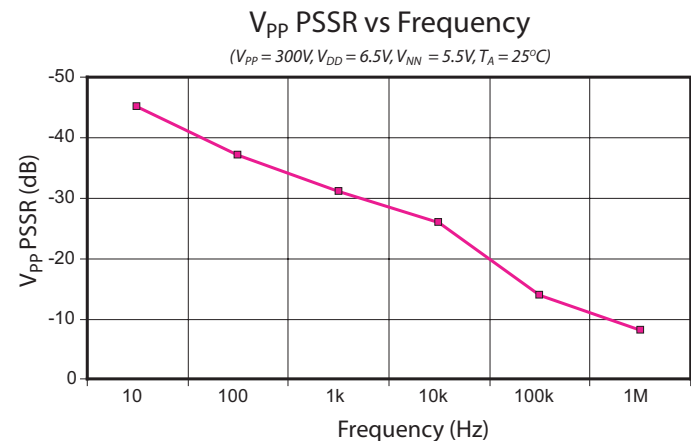
a gain of 72). The analog and digital ground traces on the PCB should be physically separated to reduce digital switching noise degrading the signal to noise performance.



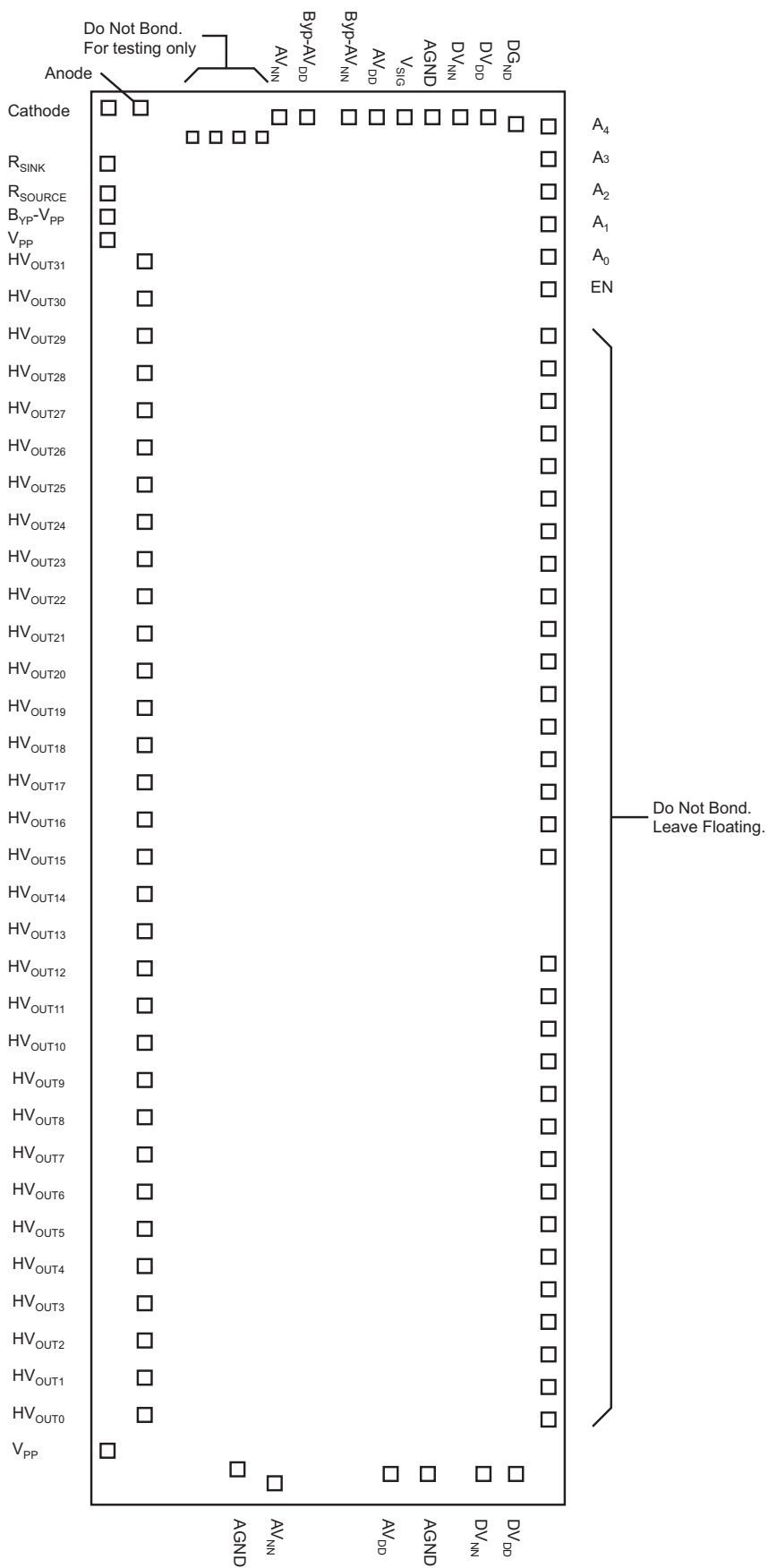
Typical Characteristics



Typical Characteristics (cont.)



Pad Configuration *(not drawn to scale)*



Pad Coordinates

Chip size: 17160 μ m x 5830 μ m

Center of die is (0,0)

Pad Name	X (μ m)	Y (μ m)
V _{PP}	-8338.5	2708.5
HV _{OUT} 0	-7895.0	2305.5
HV _{OUT} 1	-7448.5	2305.5
HV _{OUT} 2	-7001.5	2305.5
HV _{OUT} 3	-6554.5	2305.5
HV _{OUT} 4	-6107.5	2305.5
HV _{OUT} 5	-5660.5	2305.5
HV _{OUT} 6	-5213.5	2305.5
HV _{OUT} 7	-4766.5	2305.5
HV _{OUT} 8	-4319.5	2305.5
HV _{OUT} 9	-3872.5	2305.5
HV _{OUT} 10	-3425.5	2305.5
HV _{OUT} 11	-2978.5	2305.5
HV _{OUT} 12	-2531.5	2305.5
HV _{OUT} 13	-2084.5	2305.5
HV _{OUT} 14	-1637.5	2305.5
HV _{OUT} 15	-1190.5	2305.5
HV _{OUT} 16	-743.5	2305.5
HV _{OUT} 17	-296.5	2305.5
HV _{OUT} 18	150.0	2305.5
HV _{OUT} 19	597.5	2305.5
HV _{OUT} 20	1044.5	2305.5
HV _{OUT} 21	1491.5	2305.5
HV _{OUT} 22	1938.5	2305.5
HV _{OUT} 23	2385.5	2305.5
HV _{OUT} 24	2832.5	2305.5
HV _{OUT} 25	3279.5	2305.5
HV _{OUT} 26	3726.5	2305.5
HV _{OUT} 27	4173.5	2305.5
HV _{OUT} 28	4620.5	2305.5
HV _{OUT} 29	5067.5	2305.5

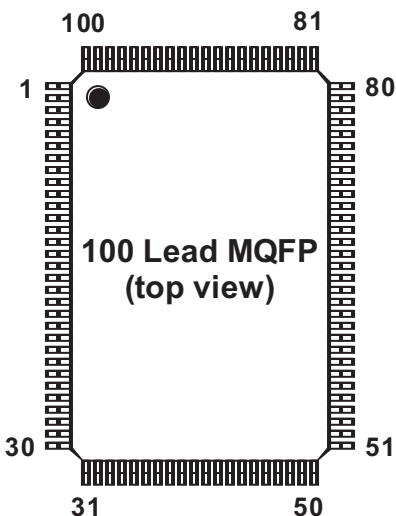
Pad Name	X (μ m)	Y (μ m)
HV _{OUT} 30	5514.5	2305.5
HV _{OUT} 31	5961.5	2305.5
V _{PP}	6659	2709
Byp_V _{PP}	7045	2709
R _{SOURCE}	7489	2709
R _{SINK}	7969	2709
Cathode	8366	2709
Anode	8366	2199
AV _{NN}	8047	425.0
Byp_AV _{DD}	8047	125.5
Byp_AV _{NN}	8047	-345.5
AV _{DD}	8047	-704.5
VSIG	8047	-1072.5
AGND	8047	-1424.5
DV _{NN}	8066.5	-1590.0
DV _{DD}	8066.5	-1958.5
DGND	7867.0	-2192.0
A ₄	7723	-2684.0
A ₃	7319.0	-2684.0
A ₂	6913.0	-2684.0
A ₁	6508.5	-2684.0
A ₀	6103.0	-2684.0
EN	5698.0	-2684.0
NC	5043.5	-2686.0
NC	4638.5	-2686.0
NC	4233.5	-2686.0
NC	3828.5	-2686.0
NC	3423.5	-2686.0
NC	3018.5	-2686.0
NC	2613.5	-2686.0
NC	2208.5	-2686.0

Pad Name	X (μ m)	Y (μ m)
NC	1803.5	-2686.0
NC	1398.5	-2686.0
NC	993.5	-2686.0
NC	588.5	-2686.0
NC	183.5	-2686.0
NC	-221.5	-2686.0
NC	-626.5	-2686.0
NC	-1031.5	-2686.0
NC	-1436.5	-2686.0
NC	-2412.0	-2686.0
NC	-2817	-2686.0
NC	-3222	-2686.0
NC	-3627	2686.0
NC	-4032	2686.0
NC	-4437	-2686.0
NC	-4842	-2686.0
NC	-5247	-2686.0
NC	-5652	-2686.0
NC	-6052	-2686.0
NC	-6462	-2686.0
NC	-6867	-2686.0
NC	-7272	-2686.0
NC	-7677	-2686.0
NC	-8082	-2686.0
DV _{DD}	-8373.0	-2250.0
DV _{NN}	-8373.0	-1949.0
AGND	-8367.0	-1561.0
AV _{DD}	-8387.0	-1143.0
AV _{NN}	-8338.5	577.5
AGND	-8341.0	916.5

Pin Description

Pin #	Function	Description
33,100	V_{PP}	High voltage positive supply. There are two pads.
99	$B_{YP} \cdot V_{PP}$	For additional V_{PP} decoupling capacitor.
42,91	AV_{DD}	Analog low voltage positive supply. This should be at the same potential as DV_{DD} . There are two pads.
93	$B_{YP} \cdot AV_{DD}$	For additional AV_{DD} decoupling capacitor.
40,94	AV_{NN}	Analog low voltage negative supply. This should be at the same potential as DV_{NN} . There are two pads.
92	$B_{YP} \cdot AV_{NN}$	For additional AV_{NN} decoupling capacitor.
45, 87	DV_{DD}	Digital low voltage positive supply. This should be at the same potential as AV_{DD} . There are two pads.
44, 88	DV_{NN}	Digital low voltage negative supply. This should be at the same potential as AV_{NN} . There are two pads.
86	D_{GND}	Digital ground.
39, 43, 89	A_{GND}	Analog Ground. There are three pads. They need to be externally connected together.
81-85	A_0 to A_4	Decoder logic input. Addressed channel will close the sample and hold switch. Sample and hold switches for unaddressed channels are kept open.
80	EN	Active logic high input. Logic low will keep sample and hold switches open.
90	V_{SIG}	Common input signal for all 32 sample and hold circuits.
98	R_{SOURCE}	External resistor from R_{SOURCE} to V_{NN} sets output current sourcing limit. Current limit is approximately 12.5V divided by R_{SOURCE} resistor value.
97	R_{SINK}	External resistor from R_{SINK} to V_{NN} sets output current sinking limit. Current limit is approximately 12.5V divided by R_{SINK} resistor value.
95	Anode	Anode side of a low voltage silicon diode that can be used to monitor die temperature.
96	Cathode	Cathode side of a low voltage silicon diode that can be used to monitor die temperature.
1-32	HV_{OUT0} to V_{OUT31}	Amplifier outputs.
34-38, 41, 46-79	NC	No Connect

Pin Layout



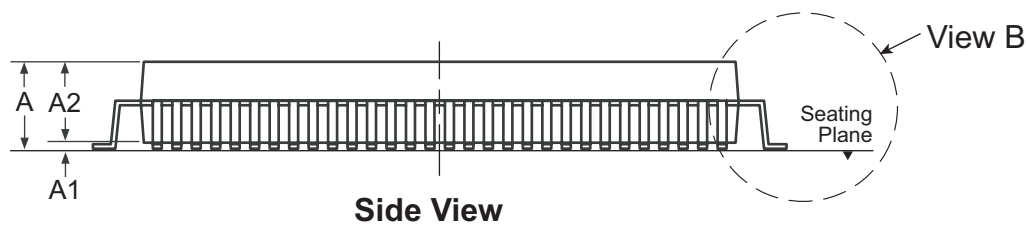
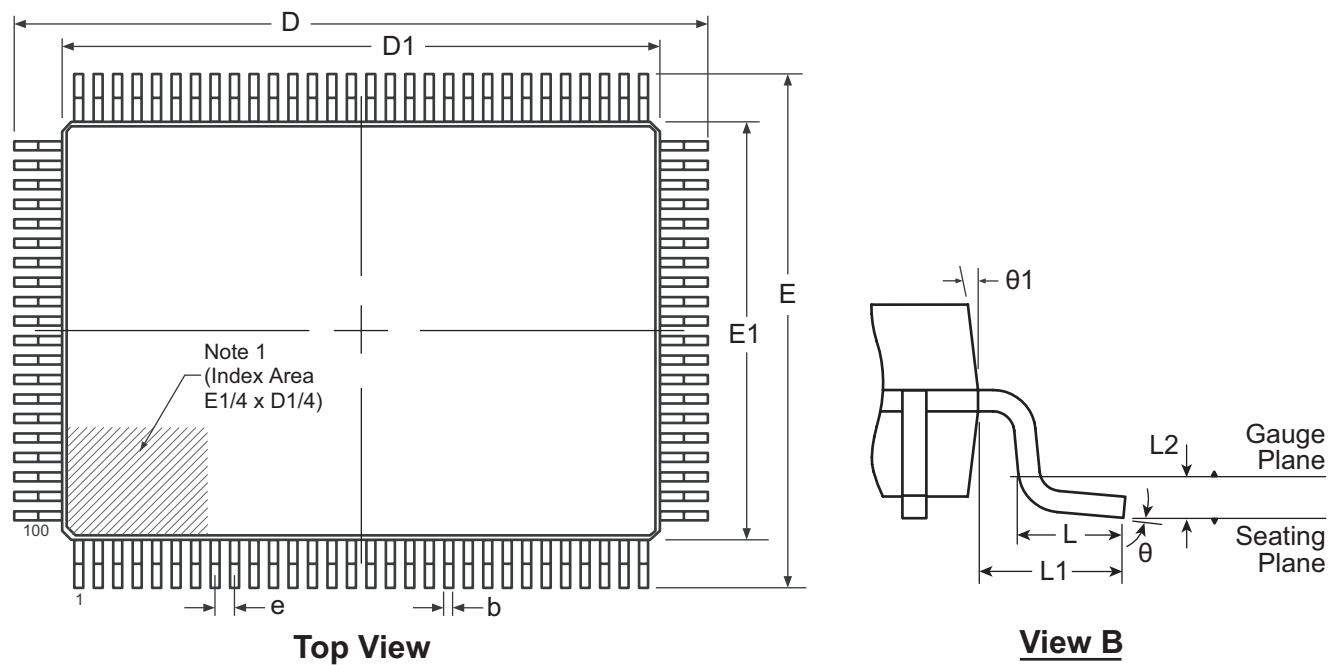
Pin Configuration

Pin	Function	Pin	Function	Pin	Function	Pin	Function
1	HV _{OUT} 31	26	HV _{OUT} 6	51	NC	76	NC
2	HV _{OUT} 30	27	HV _{OUT} 5	52	NC	77	NC
3	HV _{OUT} 29	28	HV _{OUT} 4	53	NC	78	NC
4	HV _{OUT} 28	29	HV _{OUT} 3	54	NC	79	NC
5	HV _{OUT} 27	30	HV _{OUT} 2	55	NC	80	EN
6	HV _{OUT} 26	31	HV _{OUT} 1	56	NC	81	A ₀
7	HV _{OUT} 25	32	HV _{OUT} 0	57	NC	82	A ₁
8	HV _{OUT} 24	33	V _{PP}	58	NC	83	A ₂
9	HV _{OUT} 23	34	NC	59	NC	84	A ₃
10	HV _{OUT} 22	35	NC	60	NC	85	A ₄
11	HV _{OUT} 21	36	NC	61	NC	86	D _{GND}
12	HV _{OUT} 20	37	NC	62	NC	87	DV _{DD}
13	HV _{OUT} 19	38	NC	63	NC	88	DV _{NN}
14	HV _{OUT} 18	39	A _{GND}	64	NC	89	A _{GND}
15	HV _{OUT} 17	40	AV _{NN}	65	NC	90	V _{SIG}
16	HV _{OUT} 16	41	NC	66	NC	91	AV _{DD}
17	HV _{OUT} 15	42	AV _{DD}	67	NC	92	B _{YP} -AV _{NN}
18	HV _{OUT} 14	43	A _{GND}	68	NC	93	B _{YP} -AV _{DD}
19	HV _{OUT} 13	44	DV _{NN}	69	NC	94	AV _{NN}
20	HV _{OUT} 12	45	DV _{DD}	70	NC	95	Anode
21	HV _{OUT} 11	46	NC	71	NC	96	Cathode
22	HV _{OUT} 10	47	NC	72	NC	97	R _{SINK}
23	HV _{OUT} 9	48	NC	73	NC	98	R _{SOURCE}
24	HV _{OUT} 8	49	NC	74	NC	99	B _{YP} -V _{PP}
25	HV _{OUT} 7	50	NC	75	NC	100	V _{PP}

Note: NC = No Connect

100-Lead MQFP Package Outline (FG)

20x14mm body, 3.15mm height (max.), 0.65mm pitch, 3.2mm footprint



Note 1:

A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier may be either a mold, or an embedded metal or marked feature.

Symbol		A	A1	A2	b	D	D1	E	E1	e	L	L1	L2	θ	θ1
Dimension (mm)	MIN	2.50	0.00	2.50	0.22	22.95	19.80	16.95	13.90	0.65 BSC	0.73	1.60 REF	0.25 BSC	0°	5°
	NOM	-	-	2.70	-	23.20	20.00	17.20	14.00		0.88			-	-
	MAX	3.15	0.25	2.90	0.40	23.45	20.20	17.45	14.20		1.03			7°	16°

JEDEC Registration MS-022, Variation GC-2, Issue B, Dec. 1996.

Drawings not to scale.

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